

4. The semiconductor device according to claim 2, wherein said capacitance element includes two conductive layers and a dielectric material layer, said two conductive layers positioned apart from each other on said insulating film, and said dielectric layer is formed in the clearance between the two

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10. The semiconductor device according to claim 1,

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wherein said thin film passive element includes two terminal electrodes, at least one of said two terminal electrodes of said thin film passive element being electrically connected to said connection pad.

10 11. The semiconductor device according to claim 1, wherein said thin film passive element includes two terminal electrodes, each of said terminal electrodes of said thin film passive element being electrically connected to at least one of said connection pad and said columnar electrode.

12. The semiconductor device according to claim 1, wherein the periphery of said thin film passive element is covered with a protective film.

15 13. The semiconductor device according to claim 1, which further includes a plurality of said thin film passive elements.

14. A method of manufacturing a semiconductor device comprising:

20 preparing a semiconductor wafer substrate including a plurality of chip forming regions each having a circuit element-forming region and a plurality of connection pads;

forming an insulating film on the circuit element-forming region of each of said chip forming regions;

25 forming at least one thin film passive element including at least one conductive layer on said insulating film;

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forming a dielectric material layer on said first  
conductive layer; and

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forming two pieces of conductive layer positioned adjacent to each other a predetermined distance apart from each other on said insulating film; and

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20. The method of manufacturing a semiconductor device according to claim 19, wherein said forming of the inductance element comprises patterning said conductive layer in any of the shapes selected from the group consisting of an angular eddy shape, a rectangular wave shape and a loop shape.

21. The method of manufacturing a semiconductor device according to claim 20, wherein said forming of the inductance element comprises forming a magnetic

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